Paszkiewicz Regina

List of Publications by Year
in descending order

49	225	1040056 9	1058476 14
papers	citations	h-index	g-index

49	49	49	298
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	AlGaN/GaN Heterostructures Electrical Performance by Altering GaN/Sapphire Buffers Growth Pressure and Lowâ€Temperature GaN Interlayers Application. Crystal Research and Technology, 2021, 56, 2100090.	1.3	1
2	Metalorganic vapour-phase epitaxy of AlGaN/GaN heterostructures on chlorine plasma etched GaN templates without buried conductive layer. Materials Science in Semiconductor Processing, 2020, 107, 104816.	4.0	3
3	Growth Uniformity in Selective Area Epitaxy of AlGaN/GaN Heterostructures for the Application in Semiconductor Devices. Electronics (Switzerland), 2020, 9, 2129.	3.1	5
4	Two-stage reactive ion etching of AlGaN/GaN high electron mobility transistor type heterostructures. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 011204.	1.2	1
5	Surface electrical characterization of defect related inhomogeneities of AlGaN/GaN/Si heterostructures using scanning capacitance microscopy. Materials Science in Semiconductor Processing, 2019, 94, 57-63.	4.0	7
6	Nanostructuring of Si substrates by a metal-assisted chemical etching and dewetting process. RSC Advances, 2018, 8, 31224-31230.	3.6	13
7	Substrate Effect in Electron Beam Lithography. Advances in Electrical and Electronic Engineering, 2018, 16, .	0.3	0
8	SbSI Nanosensors: from Gel to Single Nanowire Devices. Nanoscale Research Letters, 2017, 12, 97.	5.7	23
9	Self-organization of palladium nanoislands on GaN and Al x Ga 1â^'x N/GaN heterostructures. Applied Surface Science, 2017, 426, 123-132.	6.1	4
10	Proximity Effect in Gate Fabrication Using Photolithography Technique. Advances in Electrical and Electronic Engineering, 2017, 15, .	0.3	1
11	Stress control by micropits density variation in strained AlGaN/GaN/SiN/AlN/Si(111) heterostructures. Crystal Research and Technology, 2016, 51, 225-230.	1.3	5
12	Microanalysis of the Ti/Al and Ti/Al/Mo/Au ohmic contacts metallization to AlGaN/GaN heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1145-1149.	1.8	5
13	Scanning capacitance microscopy characterization of AIIIBV epitaxial layers. Materials Science-Poland, 2016, 34, 845-850.	1.0	5
14	SbSI nanowires for ferroelectric generators operating under shock pressure. Materials Letters, 2016, 180, 15-18.	2.6	19
15	Surface topography analysis with application of roughness area dependence method. Ultramicroscopy, 2016, 170, 77-85.	1.9	9
16	Comparison of electrical, optical and structural properties of epitaxially grown HEMT's type AlGaN/AlN/GaN heterostructures on Al2O3, Si and SiC substrates. Superlattices and Microstructures, 2016, 100, 619-626.	3.1	13
17	Growth and coalescence control of inclined c-axis polar and semipolar GaN multilayer structures grown on Si(111), Si(112), and Si(115) by metalorganic vapor phase epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 051504.	2.1	1
18	Formation Process and Properties of Ohmic Contacts Containing Molybdenum to AlGaN/GaN Heterostructures. Advances in Electrical and Electronic Engineering, 2016, 14, .	0.3	2

#	Article	IF	Citations
19	Application of Cl2/BCl3/Ar Plasma Treatment in the Improvement of Ti/Al/Mo/Au Ohmic Contacts. Advances in Electrical and Electronic Engineering, 2016, 14, .	0.3	1
20	Electron Beam Lithography Double Step Exposure Technique for Fabrication of Mushroom-Like Profile in Bilayer Resist System. Journal of Electrical Engineering, 2015, 65, 381-385.	0.7	1
21	GaN/AlN superlattice high electron mobility transistor heterostructures on GaN/Si(111). Physica Status Solidi (B): Basic Research, 2015, 252, 1195-1200.	1.5	4
22	Stress engineering in GaN structures grown on Si(111) substrates by SiN masking layer application. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	10
23	Optimization of AlGaN/GaN/Si(111) buffer growth conditions for nitride based HEMTs on silicon substrates. Journal of Crystal Growth, 2015, 414, 248-253.	1.5	16
24	Different buffer approaches for AlGaN/GaN heterostructures epitaxy on Si(111) substrates. , 2014, , .		0
25	Phase retrieval from the optical vortex scanning microscopy. , 2014, , .		1
26	Correlation of Selected Problems During Gan Movpe Epitaxy on si Substrates with inâ€“Situ Interferometer Observation. Journal of Electrical Engineering, 2014, 65, 294-298.	0.7	3
27	Stability of ZnO nanofibers in processing liquid agents. Materials Science-Poland, 2013, 31, 312-317.	1.0	2
28	Influence of growth process scheme on the properties of AlGaN/AlN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 306-310.	0.8	6
29	Nondestructive method for evaluation of electrical parameters of AlGaN/GaN HEMT heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 490-493.	0.8	12
30	Application nanoindenter as nanolithography tool. , 2011, , .		0
31	Atomic force microscopy for low dimensional metal strips creation and measurements. , 2011, , .		0
32	The influence of contact mode on resolution in UV 400 lithography. , 2011, , .		1
33	The selection of gas chemistry in reactive ion etching of AlGaN/GaN heterostructures. , 2011, , .		0
34	A novel electrospun ZnO nanofibers biosensor fabrication. Sensors and Actuators B: Chemical, 2011, 160, 1413-1418.	7.8	41
35	Creation of high resolution pattern by nanoscratching. Open Physics, 2011, 9, .	1.7	1
36	Influence of hydrogen absorption on stress changes in thin catalytic metal films dedicated for sensors application. Open Physics, 2011, 9, .	1.7	1

#	Article	IF	Citations
37	Investigation of the influence of low-concentration hydrogen on the surface potential of thin metallic films for sensor applications. Open Physics, 2011, 9, .	1.7	0
38	Application of AFM microscope as a nanolithography tool. , 2010, , .		0
39	Surface preparation for gallium nitride thick layers deposition by HVPE. , 2009, , .		0
40	Properties of GaN layers deposited on (0001) sapphire templates. , 2008, , .		1
41	Impact of the initial stage of deposition conditions on the properties of subsequent GaN Layer. , 2007, , .		0
42	Simulation of the influence of grain structure of heteroepitaxial nitrides layers on the performance of MSM detector. , 2007, , .		0
43	Characterization of Ar+ based Ion Beam Etching of GaN. , 2006, , .		0
44	Characterisation of AlGaN MSM by Light Beam Induced Current technique. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 602-606.	0.8	2
45	Functionally Graded Structures of AIII-BV(N) Materials for Detectors. , 2006, , .		0
46	<title>Applications of GaN-based materials in modern optoelectronics</title>. , 2004, , .		5
47	Application of GaN laterally overgrown on sapphire. , 2001, , .		0
48	Optical properties of GaN layers grown by MOCVD. , 2001, 4413, 37.		0
49	<title>Photoluminescence of GaAs grown by liquid phase epitaxy from Bi solution</title>. , 1997, , .		0